

## P-Channel 30-V (D-S) MOSFET

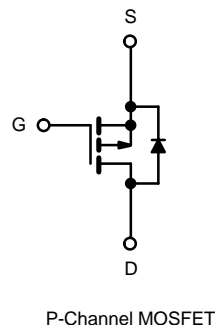
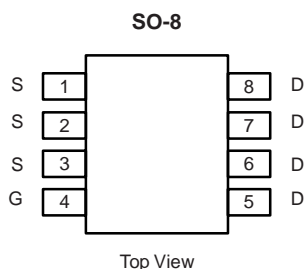
PRODUCT SUMMARY		
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
- 30	0.033 at V <sub>GS</sub> = - 10 V	- 5.8
	0.043 at V <sub>GS</sub> = - 6 V	- 5.0
	0.056 at V <sub>GS</sub> = - 4.5 V	- 4.4

### FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available



ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted				
Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage	V <sub>DS</sub>	- 30		V
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	I <sub>D</sub>	T <sub>A</sub> = 25 °C	- 5.8	- 4.1
		T <sub>A</sub> = 70 °C	- 4.6	- 3.2
Pulsed Drain Current	I <sub>DM</sub>	- 30		A
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	- 2.3	- 1.1	
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	T <sub>A</sub> = 25 °C	2.5	1.3
		T <sub>A</sub> = 70 °C	1.6	0.8
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	t ≤ 10 s	40	50	°C/W
		Steady State	70	95	
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	24	30		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

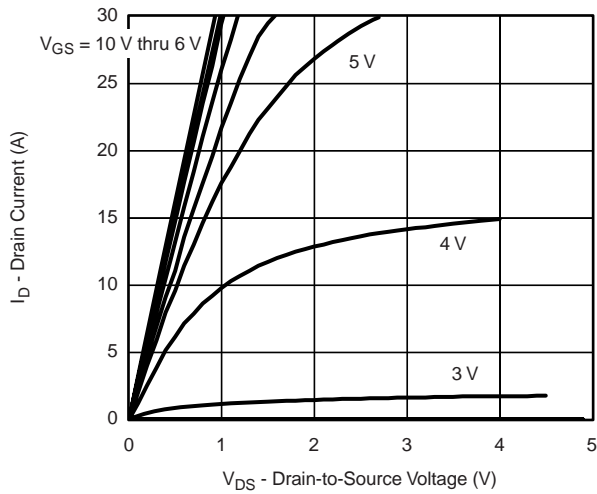
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.7		-2.0	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			-5	
On-State Drain Current <sup>b</sup>	$I_{D(on)}$	$V_{DS} \leq -10\text{ V}, V_{GS} = -10\text{ V}$	-20			A
		$V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$	-5			
Drain-Source On-State Resistance <sup>b</sup>	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -5.8\text{ A}$		0.033		$\Omega$
		$V_{GS} = -6\text{ V}, I_D = -5\text{ A}$		0.043		
		$V_{GS} = -4.5\text{ V}, I_D = -4.4\text{ A}$		0.056		
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = -15\text{ V}, I_D = -5.8\text{ A}$		13		S
Diode Forward Voltage <sup>b</sup>	$V_{SD}$	$I_S = -2.3\text{ A}, V_{GS} = 0\text{ V}$		-0.8	-1.1	V
<b>Dynamic<sup>a</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}, I_D = -3.5\text{ A}$		16	24	nC
Gate-Source Charge	$Q_{gs}$			2.3		
Gate-Drain Charge	$Q_{gd}$			4.5		
Gate Resistance	$R_g$			8.8		$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_g = 6\text{ }\Omega$		14	25	ns
Rise Time	$t_r$			14	25	
Turn-Off Delay Time	$t_{d(off)}$			42	70	
Fall Time	$t_f$			30	50	
Source-Drain Reverse Recovery Time	$t_{rr}$		$I_F = -1.2\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		30	

Notes:

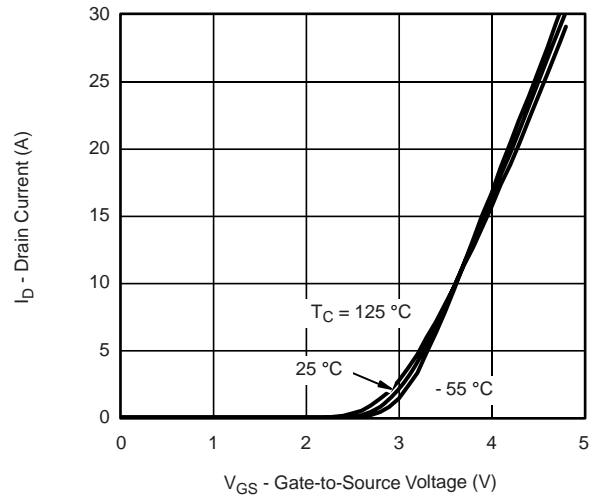
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

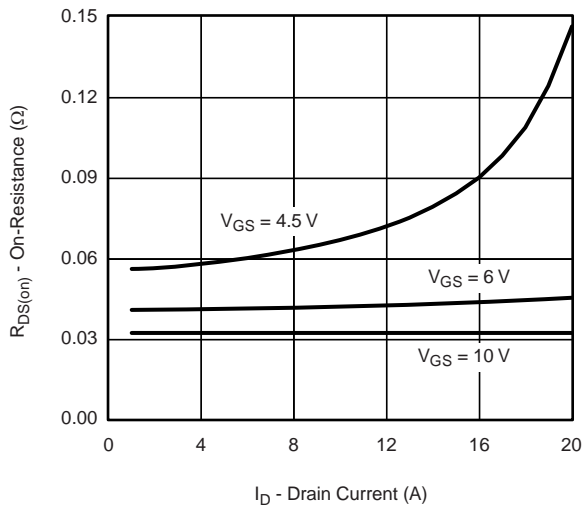
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



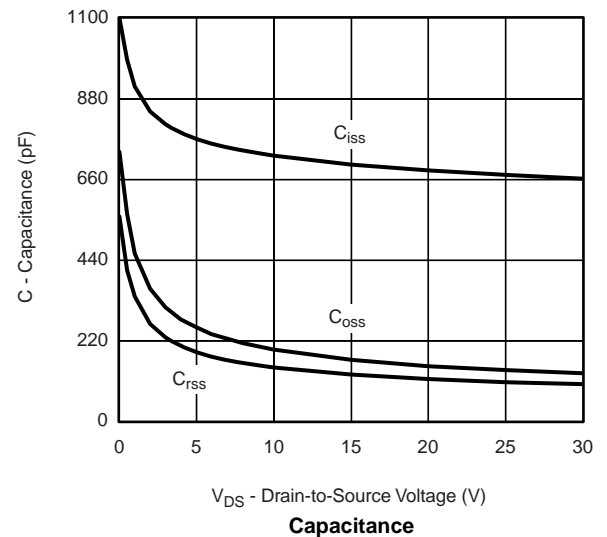
**Output Characteristics**



**Transfer Characteristics**



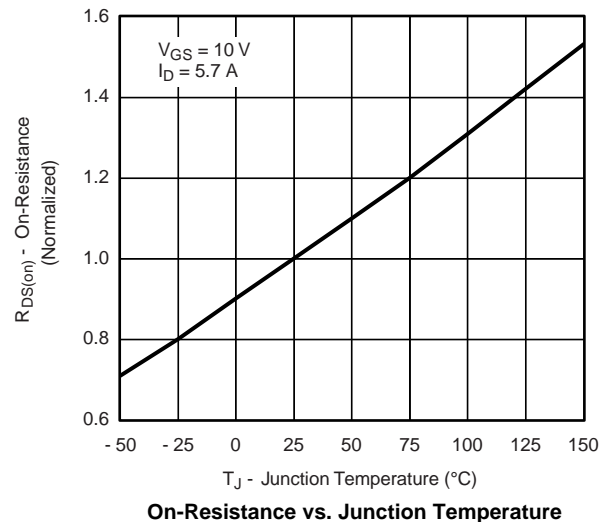
**On-Resistance vs. Drain Current**



**Capacitance**

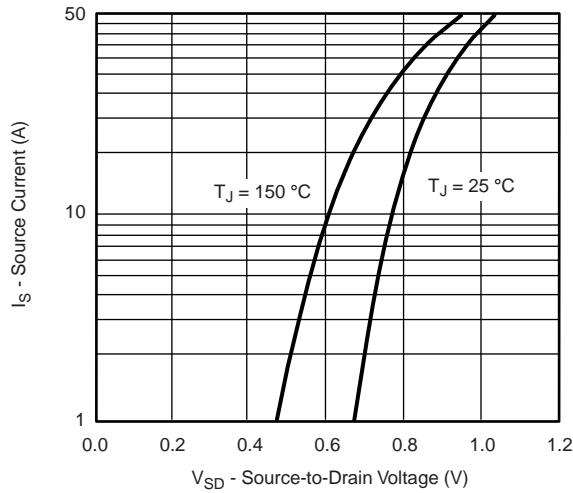


**Gate Charge**

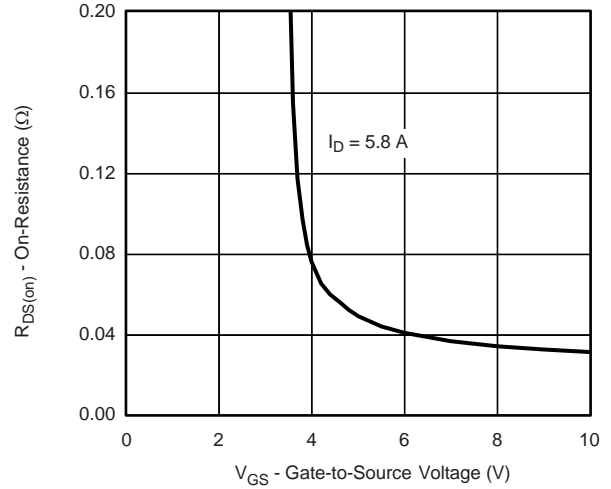


**On-Resistance vs. Junction Temperature**

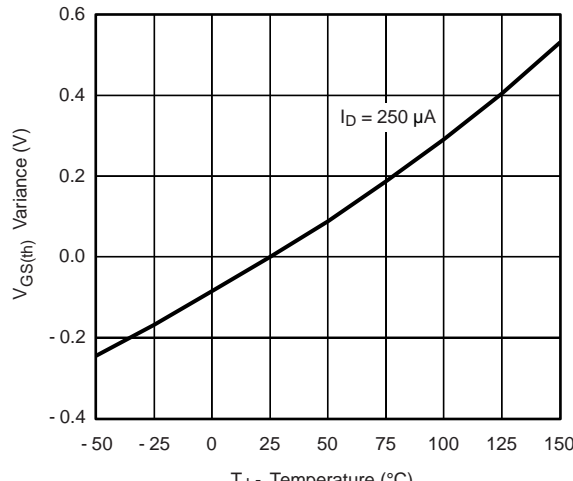
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



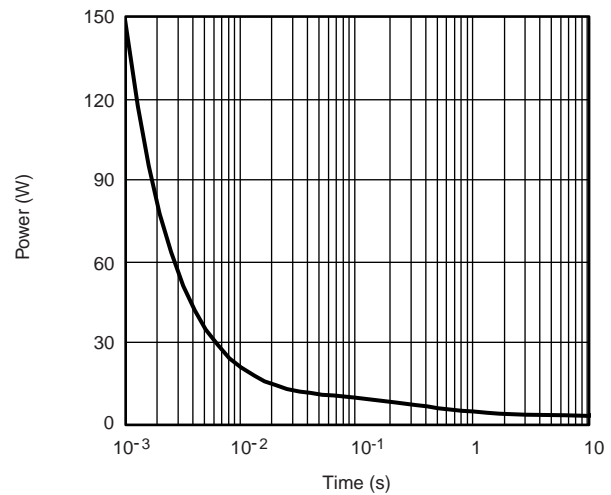
**Source-Drain Diode Forward Voltage**



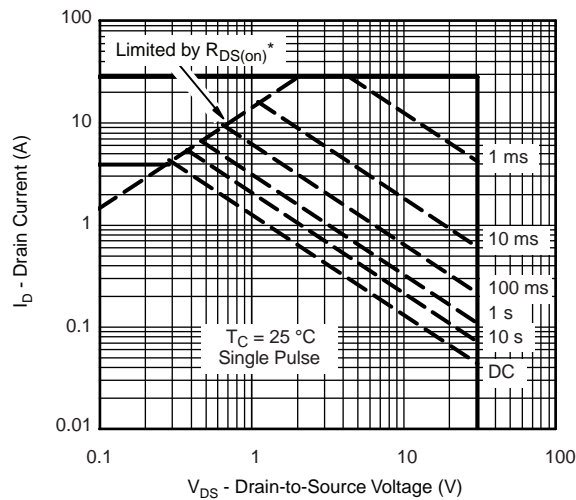
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



**Single Pulse Power, Junction-to-Ambient**



\*  $V_{DS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

**Safe Operating Area, Junction-to-Foot**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



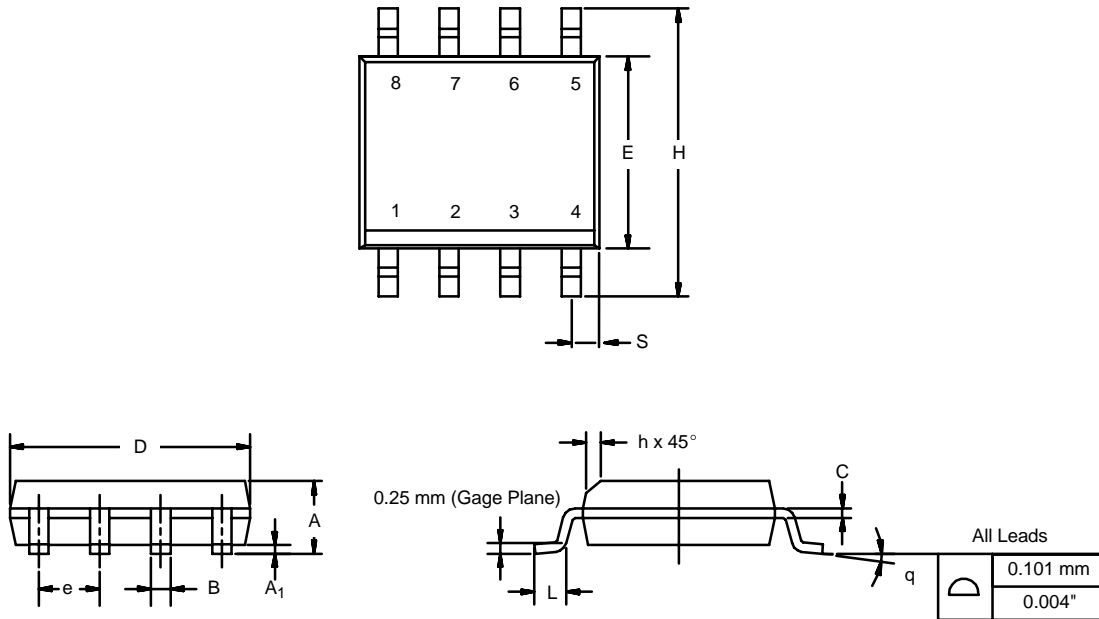
**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Foot**

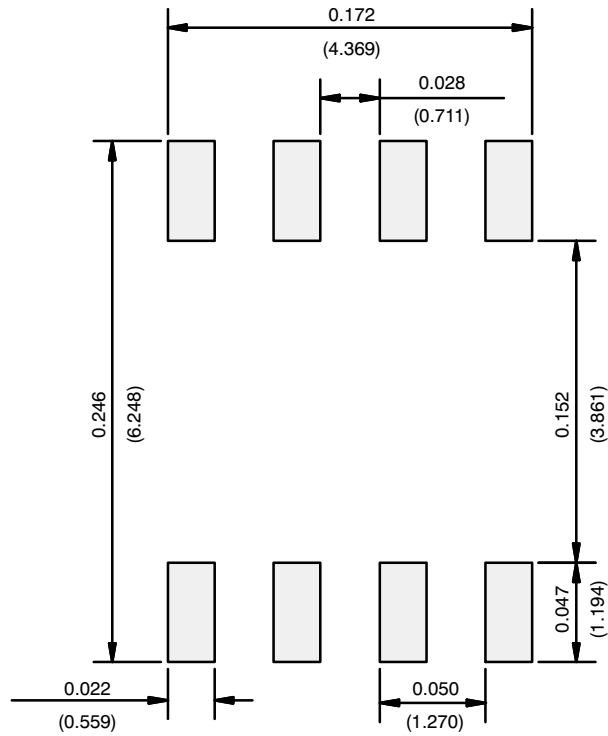
## SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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